

1                    **AMENDMENTS TO THE SPECIFICATION**

2                    Please amend the specification of the present application as set forth below.

3                    In accordance with the PTO's revised amendment format, changes are shown by  
4                    strikethrough (for deleted matter) or underlining (for added matter).

6                    In the title, please replace the title with the following title:

7                    **METHOD FOR MAKING A SEMICONDUCTOR DEVICE**  
8                    **WITH DEPOSITED OXIDE**

10                  Please replace paragraph [0028] with the following amended paragraph:

11                  [0028] A pre-diffusion clean step is performed and a polysilicon layer 40 is formed upon  
12                  patterned, deposited oxide layer 36 as seen in Figure 3. In Figure 4, polysilicon layer 40  
13                  is patterned to expose semiconductor substrate 34 through gate oxide 33 where active  
14                  regions 37, 38 are formed. Active regions 37, 38 can be formed by implanting an N+  
15                  dopant into semiconductor substrate 34 which may have a p-type doping. The patterning  
16                  of polysilicon layer 40 results in the formation of a gate oxide 33 associated with an  
17                  electrode 842. The threshold voltage for gate electrode 42 increases away from active  
18                  regions 37, 38 underneath each patterned, deposited oxide layers 36. As such, patterned,  
19                  deposited oxide layers 36 have the same electrical effect as a pair of field oxide regions  
20                  but without the detrimental problem of dopant depletion inherent to field oxide growth.